

Measurement of half-bridge parasitic impedances using a flexible test probe

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Abstract. The use of SiC MOSFETs in power applications allows to increase power density and efficiency because switching frequencies are higher. However, parasitic impedances are responsible for oscillations that can have negative effects.

In this paper we analyse the parasitic impedances of a half-bridge formed by a busbar PCB laminated with SiC MOSFETs. Using the distributed parameter approach, we have developed a procedure to characterize the impedance of the switching current loop responsible for the oscillations in the switching. According to the above, the conclusions obtained will be presented.

Key words. SiC inverter, parasitic impedance, half-bridge.

1. Introduction

Emerging wide bandgap (WBG) semiconductor materials, such as silicon carbide (SiC), can switch higher frequencies than silicon (Si)-based semiconductors; therefore, they allow high power densities and efficiency in inverters. Currently, there is a growing use of SiC MOSFETs for power applications. WBG semiconductors operate at higher voltages, temperatures, and switching frequencies than Si IGBTs. This allows power converters based on SiC devices to achieve higher power density, with lower heat dissipation requirements. SiC MOSFETs have lower parasitic capacities between the connections of drain, source and gate regions than their Si-based counterparts [1], which enables shorter timeframes for voltage and current switching. However, this leads to very high voltage (dv/dt) and current (di/dt) variations [2]: dv/dt reaches 88 V/ns and di/dt 4.4 A/ns for SiC MOSFETs. As a result, unwanted overvoltages and oscillations (up to 100 MHz [1]), can occur during SiC MOSFETs switching due to the excitation of the parasitic capacitance and inductance in the commutation loop. Therefore, the SiC MOSFET-based inverter design requires to minimize parasitic impedance [3]. In power switched converters like a half bridge, the commutation current loop impedance (Z_{CCL}) [4] depends on the parasitic impedances of the bus capacitor, SiC MOSFETs, gate drive circuits, busbars, and the tracks that interconnect these elements. Parasitic impedances are responsible for oscillations that can have negative effects limiting the designs of converters with SiC MOSFETs [5].

For an optimal converter design, it is important to have techniques to characterize parasitic impedances in the frequency domain, both in the gate circuit and in the commutation current loop, to predict oscillations and model negative effects. Parasitic impedances can be characterized experimentally or through electromagnetic simulation using different numerical methods that consider the PCB geometry and materials. For simulation estimation of parasitic impedances, there are two methods: Partial Element Equivalent Circuit (PEEC) [6],[7] and Finite Element Analysis (FEA) [4],[8]. However, these numerical methods require precise knowledge of the geometry, materials used, and their properties to obtain accurate results. Impedance in the frequency domain can be measured using an impedance analyser or a Vector Network Analyser (VNA). Both of them have been used to characterize the parasitic impedance of the switching loop in three-phase inverters [8]-[10] and parasitic impedances in low power converters. However, they require fixed test setups specifically designed for each measurement, using fixed test fixtures. This work proposes a procedure to characterize the parasitic impedances of the switching current loop Z_{CCL} .

2. Impedance measurement with VNA

A. Parasitic flexible test probe

For the characterization and study of parasitic impedances in PCBs, a shielded flexible probe (Fig. 1) has been developed [11].

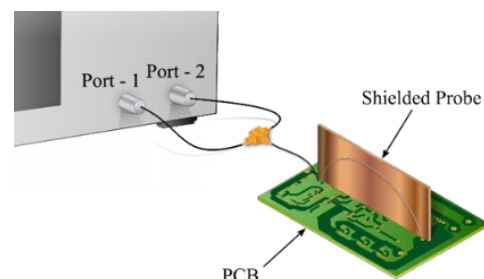


Fig. 1. Experimental setup with the flexible test probe [11].

The impedance characterization is based on a test fixture (flexible test probe) whose measuring terminals can be spaced up few cm apart. The probe consists of a pigtail coaxial cable and an RG-316/U ground coaxial that allows the return to ground of the current. The pigtail terminates in an SMA connector at one end while the other is open. The ground cable is a movable part of the probe that allows connect different points of the PCB, avoiding the need to develop a fixed test fixture for each measurement. However, the probe is located on a conductive, insulated plane perpendicular to the horizontal plane of the PCB where measurements are to be taken. The function of this conductive plane is to shield the magnetic field whose source is the current flowing during frequency scanning with the VNA. It should be noted that during calibration and measurement, both the VNA cables and the pigtail must remain in the same position to avoid unacceptable errors.

B. Two-port measurement with VNA

VNA characterizes impedance in the range from hundreds of kHz to GHz, through S-parameters. The accuracy of the measurement method depends on the range of impedance measured [12]. In this work, a two-port configuration is used with the device under test (DUT) connected in shunt, allowing the characterization of low impedances (250 $\mu\Omega$ - 25 Ω) such as those found in PCB traces in the MHz range with a maximum error of 10%. Due to the test fixture (cables, probes, and connectors) between the VNA and measurement points, there is an error in impedance measurement which can be eliminated through a prior calibration. In this work, the SOL calibration standard has been used (short circuit (S), open circuit (O), and 50 Ω (L)).

3. Half bridge impedances

In the kW range, a PCB inverter uses copper planes to distribute the bus voltage in the busbar. The busbar studied in this work consists of two rectangular copper planes, parallel, with thickness t (35 μm), length ℓ (100 mm), and width w (50 mm) separated by the thickness of the PCB d (1.6 mm). This structure forms a transmission line (TL).

A. Busbar

A transmission line is described by its characteristic impedance Z_0 and propagation constant γ

$$Z_0(\omega) = \sqrt{\frac{R' + j\omega L'}{G' + j\omega C'}} \quad (1)$$

$$\gamma(\omega) = \sqrt{(R' + j\omega L') \cdot (G' + j\omega C')} \quad (2)$$

where $\omega = 2\pi f$ and the parameters R' , L' , C' y G' are resistance, inductance, capacitance, and conductance per unit length.

The parameter R' depends on the value of the skin effect frequency (f_{sk}) in the conductor as shown in the following relation

$$f_{sk} = \frac{1}{\sigma_{Cu} \cdot \mu_0 \cdot t^2} \quad (3)$$

$$R'(\omega) = \begin{cases} R'_{dc} & f < f_{sk} \\ R'_{ac} = R'_{dc} \cdot K_R & f \geq f_{sk} \end{cases} \quad (4)$$

where $\sigma_{Cu}=58 \cdot 10^6$ S/m is the conductivity of copper and μ_0 is the permeability of vacuum. The DC resistance R'_{dc} is calculated as

$$R'_{dc} = \frac{2}{\sigma_{Cu} \cdot t \cdot w} \quad (5)$$

and K_R is the AC resistance factor [13] for each conducting plane expressed as

$$K_R = \left(\frac{t}{\delta}\right) \cdot \frac{\sinh\left(\frac{2t}{\delta}\right) + \sin\left(\frac{2t}{\delta}\right)}{\cosh\left(\frac{2t}{\delta}\right) - \cos\left(\frac{2t}{\delta}\right)} \quad (6)$$

where $\delta = (2/\omega \cdot \sigma_{Cu} \cdot \mu_0)^{1/2}$ is the skin effect penetration depth.

The parameter L' can be expressed as [14]

$$L'(\omega) = L'_i(\omega) + L'_e \quad (7)$$

where L'_i is the internal inductance and L'_e is the external one. The internal inductance L'_i is due to the magnetic flux created by the current flowing through the conductor.

$$L'_i(\omega) = \frac{R'_{dc}}{\omega} \cdot K_X \quad (8)$$

where K_X is the normalized reactance of each conducting plane and is expressed as

$$K_X = \left(\frac{t}{\delta}\right) \cdot \frac{\sinh\left(\frac{2t}{\delta}\right) - \sin\left(\frac{2t}{\delta}\right)}{\cosh\left(\frac{2t}{\delta}\right) - \cos\left(\frac{2t}{\delta}\right)} \quad (9)$$

the external inductance L'_e originates from the surface current flowing through the conductors at very high frequencies

$$L'_e = \mu \frac{d}{w} \quad (10)$$

where μ is the permeability of the PCB equal to that of vacuum.

The inductance at sufficiently high frequencies can be approximated by L'_e , because L'_i decreases with frequency.

The capacitance between two parallel planes C' can be approximated by

$$C' = \varepsilon' \cdot \varepsilon_0 \cdot \frac{w}{d} \quad (11)$$

where ε_0 is the vacuum permittivity and $\varepsilon'=4.8$ is the relative permittivity of the PCB substrate.

Finally, knowing the loss tangent $\tan \delta_e=0.011$ of the substrate, the conductance G' is given by

$$G' = \omega \cdot C' \cdot \tan \delta_e \quad (12)$$

B. Half bridge circuit

The half-bridge circuit is shown in Fig. 2.

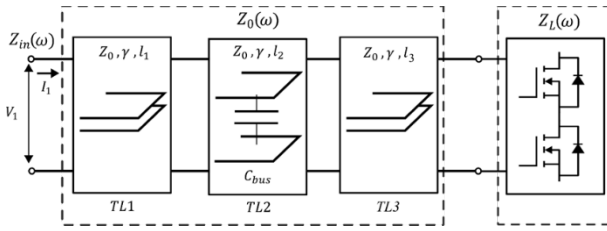


Fig. 2. The half-bridge in terms of transmission lines in cascade connection.

The busbar of the half-bridge has been divided into three cascaded transmission lines ($TL1$, $TL2$ and $TL3$) with lengths ℓ_1 , ℓ_2 y ℓ_3 . Section $TL1$ ($\ell_1=40$ mm) connects (V_{DC} to the bus capacitor C_{bus} . Section $TL2$ ($\ell_2=20$ mm) is the busbar section in parallel to C_{bus} and $TL3$ ($\ell_3=40$ mm) connects C_{bus} to the tracks connected to the SiC MOSFETs.

The input impedance Z_{in} of a TL is

$$Z_{in}(\omega) = Z_0 \cdot \frac{Z_L + Z_0 \cdot \tanh(\gamma\ell)}{Z_0 + Z_L \cdot \tanh(\gamma\ell)} \quad (13)$$

where Z_L is the equivalent load dipole and can be solved from (13) as

$$Z_L = Z_0 \cdot \frac{Z_{in} - Z_0 \cdot \tanh(\gamma\ell)}{Z_0 - Z_{in} \cdot \tanh(\gamma\ell)} \quad (14)$$

The switching current loop impedance Z_{CCL} is calculated as

$$Z_{CCL}(\omega) = Z_{Cbus} + Z_0 \frac{Z_L + Z_0 \cdot \tanh(\gamma\ell_3)}{Z_0 + Z_L \cdot \tanh(\gamma\ell_3)} \quad (15)$$

C. Load impedance

The load dipole Z_L is constituted by the elements connected to the rectangular busbar: SiC MOSFET, gate drive circuits and the tracks that interconnect them. In Fig. 3, the equivalent wye circuit of a SiC MOSFET connected with the gate circuit is shown.

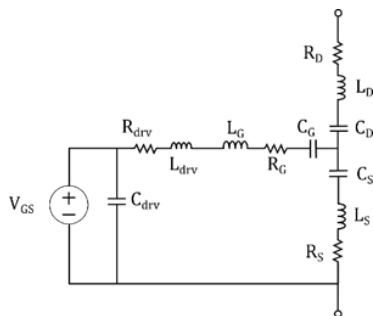


Fig. 3. SiC MOSFET circuit and gate driver assembly.

The driver impedances are: gate resistance R_{drv} , driver track inductance L_{drv} and C_{drv} , the equivalent capacitance of the voltage sources V_{GS} . The MOSFET equivalent circuit is formed by the drain capacitances, inductances and resistances (C_D , L_D y R_D), source (C_S , L_S y R_S) and drives (C_G , L_G y R_G). Additionally, R_D and R_S are of the order of $m\Omega$ and are neglected. The equivalent circuit of the SiC

MOSFET and gate driver in conduction and off state are shown in Fig. 4.

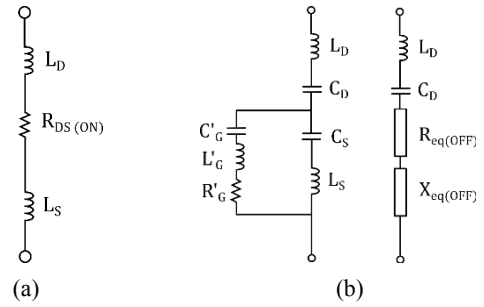


Fig. 4. Equivalent circuit of the SiC MOSFET and gate driver in conduction state (a) and off state (b).

In conduction (Fig. 4a), the conduction channel of the SiC MOSFET with resistance $R_{DS(ON)}$ is enabled, short-circuiting capacitances C_D y C_S . The MOSFET impedance in conduction $Z_{MOS(ON)}$ is

$$Z_{MOS(ON)}(\omega) = R_{DS(ON)} + j(\omega(L_D + L_S)) \quad (16)$$

From the circuit of Fig. 4b, R'_G , C'_G and L'_G are the series equivalents between the gate terminal of the SiC MOSFET (R_G , C_G and L_G) and the driver circuit (R_{drv} , C_{drv} and L_{drv}). Also, the parallel impedance between the series RLC branch formed by (C'_G , L'_G and R'_G) and the series RL branch formed by (C_S and L_S) is given by $R_{eq(OFF)}$ and $X_{eq(OFF)}$. Then the equivalent series impedance of the SiC MOSFET transistor when in off state is

$$Z_{MOS(OFF)} = R_{eq(OFF)} + j(X_D + X_{eq(OFF)}) \quad (17)$$

where X_D is the drain reactance formed by C_D and L_D .

During a switching with the upper transistor (H) in conduction and the lower transistor (L) in off state (state HL=01), the resulting circuit for Z_L is shown in Fig. 5. The equivalent partial inductance ($L_{CCL,p}$) and resistance ($R_{CCL,p}$) of the tracks that connect to the SiC MOSFET are calculated as

$$L_{CCL,p} = L_1 - \left(\frac{\text{Im}\{Z_{MOS(OFF)} + Z_{MOS(ON)}\}}{\omega} \right) \quad (18)$$

$$R_{CCL,p} = R_1 - \text{Re}\{Z_{MOS(OFF)} + Z_{MOS(ON)}\} \quad (19)$$

where L_1 and R_1 are the series RLC circuit inductance and resistance representing Z_L and are calculated with (13) from Z_{in} measurement.

4. Half-bridge characterization

The elements that make up the Z_{CCL} switching current loop are the SiC MOSFET, C_{bus} , the gate driver PCB, and the half-bridge PCB. To obtain Z_{CCL} , SiC MOSFET, C_{bus} , and gate driver are characterized separately with the half-bridge unmounted. Once, SiC MOSFET and gate driver are mounted on the half-bridge PCB, but not C_{bus} . Z_L is calculated using the measurement of Z_{in} according to (14). After that, the equivalent impedances $R_{CCL,p}$ and $L_{CCL,p}$ are calculated from (20) and (21).

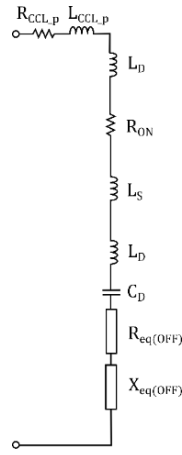


Fig. 5. Equivalent circuit of the load dipole Z_L with discret elements in the HL=10 state.

A. C_{bus} , SiC MOSFET and driver

C_{bus} is considered to be an RLC series circuit, where ESR is the equivalent series resistance, ESL is the equivalent series inductance, and C_{bus} the capacitor capacity. The impedance is obtained by using VNA.

C_{bus} is measured at low frequency 5 kHz where the capacitor predominates in the impedance and a value of 29.22 μ F is found. The ESL inductance (31.17 nH) is calculated at the resonance frequency (f_s =166.77 kHz). The ESR is 10 m Ω and considered constant.

According to the datasheet of the used SiC MOSFET (SCTW100N65G2AG), $R_{DS(ON)}$ =20 m Ω . SiC MOSFET parasitic impedances of the Table I have been characterized using a specific test setup according to the method developed in [15].

Table I. – Parasitic impedances of the SiC MOSFET

Symbol	Description	Value	Units
L_D	Drain Inductance	1,06	nH
L_G	Gate Inductance	6,76	nH
L_S	Source Inductance	4,25	nH
C_D	Drain capacitor	8,14	nF
C_G	Gate capacitor	7,57	nF
C_S	Source capacitor	2,54	nF
R_G	Gate resistor	0,85	Ω

Gate driver characterization is done using the shunt-thru two-port method and shielded flexible probes [11]. For this, the half-bridge PCB (without mounting the C_{bus} or the SiC MOSFET) is connected to a gate driver board.

After that, the shielded flexible probe is connected to the plated holes where SiC MOSFET gate (G) and source (S) terminals should be mounted as shown in Fig. 6. Measurements are done in off state.

The measured gate driver door resistance is R_{drv} =10.2 Ω , the power supply capacity C_{drv} =534 nF and L_{drv} =34,9 nH, which are in agreement with the designed ones.

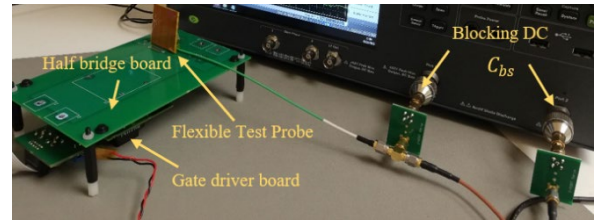


Fig. 6. Experimental setup to measure gate driver cicircuit.

B. Characterization of the load dipole

From the measurement of Z_{in} (Fig. 2), R_1 , L_1 , C_1 , and $R_{CCL,p}$ and $L_{CCL,p}$ can be calculated. Z_{in} is measured at the connection terminals with V_{DC} of the half-bridge. Measurement are carried out with the shielded flexible probe. To determine the shielded flexible probe accuracy, an SMA is included as a reference. The measurement setup is shown in Fig. 7.

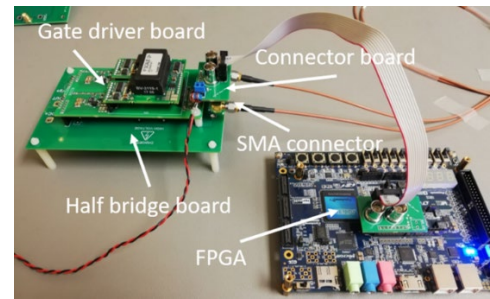


Fig. 7. Test setup for experimental characterization of the half bridge.

Fig. 8 shows the measured impedance Z_{in} and Fig. 9 shows the calculated impedance Z_L . The measurement was made using a coaxial SMA connector, with a sweep frequency from 100 kHz to 100 MHz for the different conduction states of the half-bridge transistors (HL=00, HL=01, HL=10 and HL=11), controlled by a Cyclone V GX FPGA.

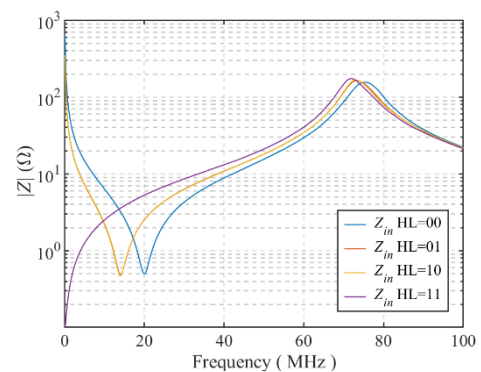


Fig. 8. Impedance Z_{in} measured using a sweep frequency from 100 kHz to 100 MHz.

From the measurement of Z_L and the resonance frequency f_s and C_1 ; L_1 and R_1 are calculated taking into account they are the components of the series RLC circuit Z_L . Next, $R_{CCL,p}$ and $L_{CCL,p}$ are obtained using (20) and (21) at the resonance frequency f_s . Results obtained are shown in Table II.

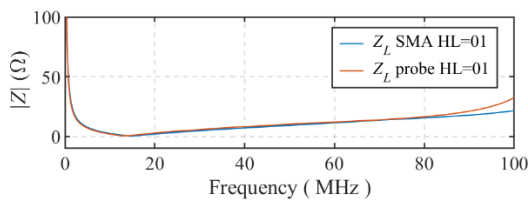


Fig. 9. Impedance Z_L calculated from 100 kHz to 100 MHz.

Table II. – Measured values of the load dipole circuit (HL=01) components

	f_s (MHz)	R_1 (Ω)	L_1 (nH)	C_1 (nF)	$R_{CCL,p}$ (Ω)	$L_{CCL,p}$ (nH)
Probe	13,19	0,514	32,477	4,483	0.496	23.094
SMA	14,76	0,459	27.903	4,167	0.453	18.521

The switching current loop impedance (Z_{CCL}) is calculated using (15) and results are shown in Fig. 11. The inductance $L_{CCL,SMA}$ calculated using the SMA connector is 55.02 nH while with the flexible probe the value obtained $L_{CCL,probe}$ is 59.36 nH. Therefore, the error with respect to $L_{CCL,SMA}$ is 7.89%.

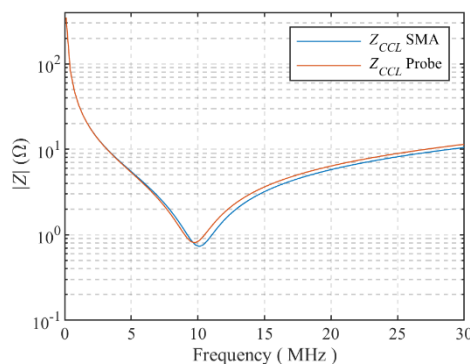


Fig. 10. Impedance measured with SMA and with flexible test probe.

5. Conclusions

A procedure for characterizing parasitic impedances of PCB SiC inverter is proposed. The analysis of a laminated PCB busbar (two parallel planes) is considered as a transmission line terminated at the load dipole Z_L . The switching current loop impedance (Z_{CCL}) calculated from the previous parasitic impedances is compared with those measured using a fixed probe based on SMA connector.

The proposed methodology error (7.89%) is acceptable and the technique can be considered as a valid alternative for determining the parasitic impedances.

Acknowledgements

The authors would like to thank the technical support from the Research Group on Renewable Energy Integration (GENER) of the University of Zaragoza (accredited and funded by the Government of Aragón).

This research has received funding from the Spanish Government MCIN/AEI/10.13039/501100011033 under grant agreement No CPP2021-008848 and from the European Union NextGenerationEU/PRTR.

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